

wherein phosphorus ion is implanted with an energy of about 100 KeV to 200 KeV in the substrate to form the layer. *object*

7, 11. (Amended) A method of manufacturing a semiconductor device according to Claim

wherein for forming the layer, ion implantation is carried out *in object again* at a region spanning from a predetermined space from said first gate insulation film to said third drain region by using a photo-resist as a mask.

8, 12. (Amended) A method of manufacturing a semiconductor device according to Claim

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H wherein for forming the layer, ion implantation is carried out *in* at a region spanning from a predetermined space from said first gate insulation film to said third drain region by using a photo-resist as a mask.

7, 13. (Amended) A method of manufacturing a semiconductor device according to Claim

wherein for forming the layer, ion implantation is carried out *in* at a region spanning from a predetermined space from the first gate insulation film to said third drain region by using a side wall insulation film formed at a side wall portion of said first gate insulating film as a mask.

8, 14. (Amended) A method of manufacturing a semiconductor device according to Claim

wherein for forming the layer, ion implantation is carried out *in* at a region spanning from a predetermined space from the first gate insulation film to said third drain region by using a side wall insulation film formed at a side wall portion of said first gate insulating film as a mask.

7, 15. (Amended) A method of manufacturing a semiconductor device according to Claim

wherein said layer is formed ⁱⁿ at a region spanning from a predetermined space from the first gate insulation film to said third drain region by using said first gate insulation film as a mask and ion-implanting obliquely from an upper side of the first gate insulation film.

16. (Amended) A method of manufacturing a semiconductor device according to Claim 8,

wherein said layer is formed ⁱⁿ at a region spanning from a predetermined space from the first gate insulation film to said third drain region by using said first gate insulation film as a mask and ion-implanting obliquely from an upper side of the first gate insulation film.

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17. (Amended) A method of manufacturing a semiconductor device according to Claim 7,

wherein said layer is formed ⁱⁿ at a region spanning from a predetermined space from the first gate insulation film to said third drain region by using a photo-resist formed to cover said first gate insulation film and ion implanting obliquely from above the first gate insulation film.

18. (Amended) A method of manufacturing a semiconductor device according to Claim 8,

wherein said layer is formed ⁱⁿ at a region spanning from a predetermined space from the first gate insulation film to said third drain region by forming a photo-resist formed to cover said first gate insulation film and ion implanting obliquely from above the first gate insulation film.

19. (Amended) A method of manufacturing a semiconductor device according to Claim 7,

wherein said first drain region has a lower impurity concentration than said second drain region.

20. (Amended) A method of manufacturing a semiconductor device according to Claim 8,

Applicant : Shuici Kikuchi et al.
Serial No. : 09/829,876
Filed : April 10, 2001
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Attorney's Docket No.: 10417-076001 / F51-
132533M/HW

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wherein said first drain region has a lower impurity concentration than said second drain
region.

In the drawings:

Please substitute Figs. 13 to 16 with the corrected drawings provided herein.